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## Electrical and Optical Studies of Doped $\text{CdF}_2$ - $\text{CaF}_2$ Crystals

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Bridgman-grown  $\text{Cd}_{1-x}\text{Ca}_x\text{F}_2$  crystals were doped with  $\text{SmF}_3$ ,  $\text{YbF}_3$ , and  $\text{YF}_3$ . X-Ray powder diffraction photographs showed complete solid solution between  $\text{CaF}_2$  and  $\text{CdF}_2$ . The crystals were fired in a Cd atmosphere at  $500^\circ$ . Electrical resistivity and Hall effect studies showed that crystals doped with 0.1 mole %  $\text{REF}_3$  and fired in Cd were n-type semiconductors with a room-temperature resistivity, carrier concentration, and mobility independent of crystal composition between 0 and 1%  $\text{CaF}_2$ . Between 1 and 10%  $\text{CaF}_2$  the resistivity increased from about 1 to about  $10^7$  ohm-cm. The intense infrared absorption, which is associated with the conductivity and which causes the blue color of the crystals, followed the same pattern. Up to 1%  $\text{CaF}_2$  the crystals were blue. With 10%  $\text{CaF}_2$  added, the crystals were colorless. Similar sharp changes in resistivity and infrared absorption were observed with  $\text{REF}_3$  dopant concentration variations. Optical absorption studies indicated  $\text{Yb}^{2+}$  ions in  $\text{CdF}_2$ -7%  $\text{CaF}_2$ -0.1%  $\text{YbF}_3$  crystals after Cd firing, but no  $\text{Sm}^{2+}$  or  $\text{Y}^{2+}$  ions were observed until the  $\text{CaF}_2$  content was very high (greater than 99.5%). The lack of correspondence between  $\text{RE}^{2+}$  formation and the cessation of conductivity are considered on the basis of chemical oxidation potentials. A model is proposed for the conductivity in which the  $\text{Cd}^{2+}$  ions nearest the  $\text{RE}^{2+}$ -substituted ion share an electron thus creating an "impurity" donor level. This model is consistent with the variations of the conductivity and of the  $\text{RE}^{2+}$  concentrations with changing  $\text{CdF}_2/\text{CaF}_2$  ratios.

### Introduction

In the last few years the optical properties of rare earths in  $\text{CaF}_2$  have been studied extensively and many optically pumped lasers have been produced.<sup>2</sup> Lasers have been made using divalent rare earth dopants such as  $\text{Sm}^{2+}$ ,  $\text{Dy}^{2+}$ , and  $\text{Tm}^{2+}$ .<sup>3,4</sup> In fact, all rare earths have been obtained in the 2+ oxidation state in  $\text{CaF}_2$  crystals and their optical properties investigated.<sup>5</sup> Recently,  $\text{CdF}_2$  crystals doped with rare earths have also shown a very interesting property. When the crystals are fired in Cd vapor at  $500^\circ$ , they change from electrical insulators (resistivity about  $10^7$  ohm-cm at  $300^\circ\text{K}$ ) to n-type semiconductors (resistivity about 1 ohm-cm at  $300^\circ\text{K}$ ).<sup>6-8</sup> Simultaneously, the crystals become deep blue in color. Although  $\text{CaF}_2$  and  $\text{CdF}_2$  show the above differences, they are also similar in many ways. For example,  $\text{CaF}_2$  and  $\text{CdF}_2$  have identical cubic structures (fluorite) with very similar lattice constants, 5.45 and 5.40 Å, respectively. Also, the ionic sizes of  $\text{Ca}^{2+}$  and  $\text{Cd}^{2+}$  are very similar, 0.99 and 0.97 Å, respectively. Consequently,  $\text{CaF}_2$  and  $\text{CdF}_2$  form a continuous series of solid solutions. This system has several interesting features. Consider the two end members. In rare earth doped  $\text{CaF}_2$ ,  $\text{RE}^{2+}$  ions can be obtained by firing in Ca vapor,<sup>9</sup> and the crystals are highly insulating. In rare earth doped  $\text{CdF}_2$ , no  $\text{RE}^{2+}$  ions that can be detected by epr or by optical absorption (except  $\text{Eu}^{2+}$ ) are produced by firing in Cd vapor. The crystals, however, exhibit electronic conductivity (except with La, Ce, Pr, and Eu doping).<sup>10</sup>

Then the  $\text{CaF}_2$ - $\text{CdF}_2$  solid solution region should contain regions of transition. At one  $\text{CaF}_2/\text{CdF}_2$  ratio  $\text{RE}^{2+}$  ions should be observable; at another ratio only  $\text{RE}^{3+}$  ions should be detected. At some  $\text{CaF}_2/\text{CdF}_2$  ratio, conductivity should be produced by firing the crystals in Cd; at another ratio no conductivity should be obtained.

In order to investigate this  $\text{CdF}_2$ - $\text{CaF}_2$  solid solution region, the following experiments were conducted. Crystals were grown by a Bridgman technique and doped with  $\text{SmF}_3$ ,  $\text{YbF}_3$ , and  $\text{YF}_3$ . Optical absorption spectra were taken at 300, 77, and  $6^\circ\text{K}$ , and the visible fluorescence, phosphorescence, and thermoluminescence under 2537- and 3660-Å excitation were observed visually. The electrical resistivity and the Hall effect were studied at 300 and  $77^\circ\text{K}$ .

### Experimental Section

**Crystal Growth and Treatment.**—The preparation of the  $\text{CdF}_2$  starting material from reagent grade  $\text{CdCO}_3$  and aqueous HF was described previously.<sup>10</sup> Powdered single-crystal sections of  $\text{CaF}_2$  (and  $\text{SrF}_2$ ,  $\text{BaF}_2$ , and  $\text{PbF}_2$  when used) also served as host starting material. Dopants were added as  $\text{SmF}_3$ ,  $\text{YbF}_3$ , and  $\text{YF}_3$  (all 99.9% purity) generally at the 0.1 mole % level. No pretreatment was used until the  $\text{CdF}_2$  content in the  $\text{CaF}_2$ - $\text{CdF}_2$  mixed crystals fell below about 1%. Then the dopants were rendered anhydrous by firing in flowing HF at about  $1000^\circ$  for several hours.

The Bridgman single-crystal growth using graphite crucibles was described previously.<sup>11</sup> The grown crystals were about 10 mm in diameter and 10 to 50 mm long. In the  $\text{CaF}_2$ - $\text{CdF}_2$  mixed crystals there was often considerable strain and some cracking. Segregation of  $\text{CaF}_2$  and  $\text{CdF}_2$  was indicated by varying ratios of  $\text{CaF}_2$  to  $\text{CdF}_2$  along the length of a crystal. However, very sharp patterns in X-ray powder diffraction photographs showed complete solid solution between  $\text{CaF}_2$  and  $\text{CdF}_2$  with Vegard's law being obeyed.

To ensure that crystal inhomogeneities did not affect the experimental measurements, slices for study were cut perpendicular to the growth direction. No variations in the  $\text{CaF}_2/\text{CdF}_2$  ratio,

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TABLE I  
RESISTIVITY, HALL COEFFICIENT, CARRIER CONCENTRATION, AND HALL MOBILITY FOR Cd<sub>1-x</sub>Ca<sub>x</sub>F<sub>2</sub>:0.1% YF<sub>3</sub>  
AND CdF<sub>2</sub>:x% YF<sub>3</sub> CRYSTALS TREATED IN Cd AT 500°

Dopant	Resistivity, $\rho$ , ohm-cm		Hall coefficient, $-R_H$ , cm <sup>3</sup> / coulomb 300°K	Carrier concn, $n$ , e <sup>-</sup> /cm <sup>3</sup> 300°K	Hall mobility, $\mu_H$ , cm <sup>2</sup> /v-sec 300°K
	300°K	77°K			
0.1% YF <sub>3</sub>	0.178	2.18	1.4	$4.4 \times 10^{18}$	7.9
0.1% YF <sub>3</sub> + 0.01% CaF <sub>2</sub>	0.162	8.6	1.4	$4.5 \times 10^{18}$	8.6
0.1% YF <sub>3</sub> + 0.1% CaF <sub>2</sub>	0.154	2.38	1.6	$4.1 \times 10^{18}$	10
0.1% YF <sub>3</sub> + 1.0% CaF <sub>2</sub>	0.188	4.21	1.8	$3.5 \times 10^{18}$	9.6
0.1% YF <sub>3</sub> + 7.0% CaF <sub>2</sub>	2.85	$2.4 \times 10^2$	12	$6 \times 10^{17}$	4.2
0.1% YF <sub>3</sub> + 10.0% CaF <sub>2</sub>	$\sim 10^7$				
0.1% YbF <sub>3</sub>	0.144	4.77	1.8	$3.6 \times 10^{18}$	13
0.1% YbF <sub>3</sub> + 3% CaF <sub>2</sub>	87				
0.1% YbF <sub>3</sub> + 7% CaF <sub>2</sub>	$2.2 \times 10^2$				
0.1% YbF <sub>3</sub> + 10% CaF <sub>2</sub>	$\sim 10^7$				
0.1% YF <sub>3</sub>	0.178	2.18	1.4	$4.4 \times 10^{18}$	7.9
1.0% YF <sub>3</sub>	2.0				
10.0% YF <sub>3</sub>	$\sim 10^7$				
20.0% YF <sub>3</sub>	$\sim 10^7$				

greater than experimental error, were detected in the electrical, optical, or X-ray studies reported in this study.

To test whether or not conductivity was produced, all crystals were fired in Cd vapor (except CaF<sub>2</sub>:M<sup>3+</sup> which was fired in Ca). The crystal and a piece of high-purity Cd metal were heated at 500° for 1 hr in a sealed, evacuated (about 10<sup>-6</sup> mm) quartz tube.

**Electrical Properties.**—The conductivity and Hall effect were measured using standard direct current techniques and apparatus at 300 and 77°K as described previously.<sup>10</sup> All of the conducting crystals measured were n type and were blue. A darker blue color indicated higher conductivity.

The electrical properties of CdF<sub>2</sub> crystals doped with Sm, Yb, and Y and fired in Cd at 500° were very similar. Table I lists the resistivity,  $\rho$ , Hall coefficient,  $R_H$ , carrier concentration,  $n$ , and Hall mobility,  $\mu_H$ , for several crystals. The data on the Sm-doped samples are not tabulated since the measurements were less accurate. Crystals doped with Sm and fired in Cd, however, were n-type conductors, and at 300°K they behaved as is shown in Figure 1 for Y doping. In Figure 1 it is seen that the resistivity at 300 and 77°K for Cd-treated crystals with a dopant concentration of 0.1 mole % YF<sub>3</sub> is essentially constant from 0 to 1% CaF<sub>2</sub> added to CdF<sub>2</sub>. Between 1 and 10% CaF<sub>2</sub>,  $\rho$  goes from about 1 ohm-cm to about 10<sup>7</sup> ohm-cm. Similar behavior is noted with the carrier concentration and mobility as is shown in Figure 2. At 1% added CaF<sub>2</sub>,  $n$  and  $\mu_H$  are about 10<sup>17</sup> e<sup>-</sup>/cm<sup>3</sup> and 10 cm<sup>2</sup>/v-sec, respectively. They both decrease as CaF<sub>2</sub> is added until at 10% CaF<sub>2</sub> they can no longer be measured. Very similar electrical results were obtained with solid solutions of CdF<sub>2</sub> and SrF<sub>2</sub> or BaF<sub>2</sub>, whereas different results were indicated for CdF<sub>2</sub>-PbF<sub>2</sub> mixtures.

Table I also shows the variation of the resistivity of Cd-fired CdF<sub>2</sub> crystals as a function of doping concentration. As is seen for the case of CdF<sub>2</sub>:x% YF<sub>3</sub> crystals, the observed behavior is quite similar to that of adding CaF<sub>2</sub>. Between 1 and 10% YF<sub>3</sub> the resistivity increases from about 2 to about 10<sup>7</sup> ohm-cm.

**Optical Properties. Infrared Absorption.**—When doped crystals are rendered conducting by firing in Cd at 500°, an associated property is the blue color of the crystals. This color is caused by strong infrared absorption; the absorption coefficient varies approximately as  $\lambda^3$ .<sup>4</sup>

Absorption spectra of selected samples before and after Cd firing were run on a Cary Model 14 spectrophotometer at 300, 77, and 6°K. Examples of these spectra are shown in Figure 3 for YbF<sub>3</sub> doping. From this figure and the data below on YF<sub>3</sub> doping it is apparent that the broad infrared absorption goes through a transition, similar to that of the conductivity, as the CaF<sub>2</sub>/CdF<sub>2</sub> ratio or dopant concentration changes. Figure 3 shows the absorption of untreated and Cd-fired crystals of Cd<sub>1-x</sub>Ca<sub>x</sub>F<sub>2</sub>:0.1% YbF<sub>3</sub> containing 0 and 7% CaF<sub>2</sub>. The 7% curves resemble

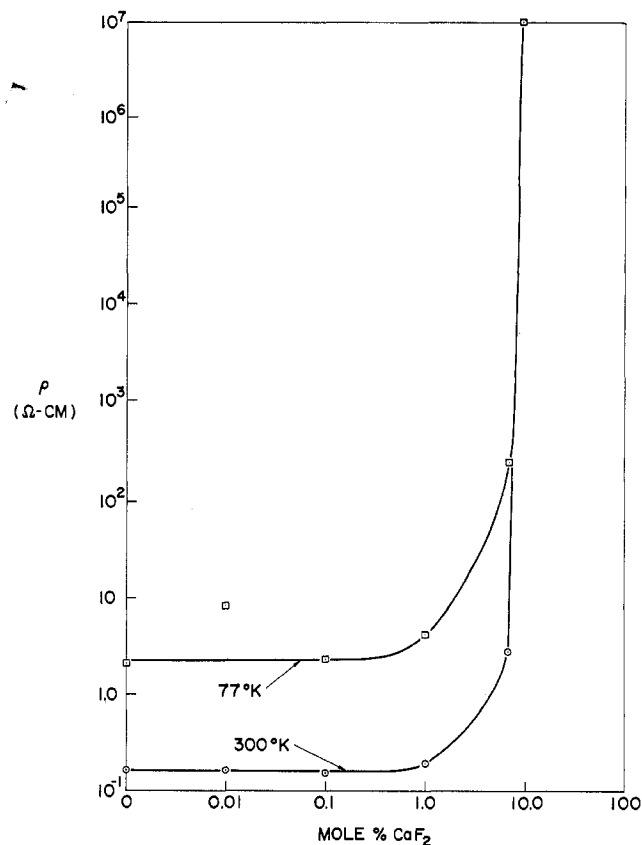


Figure 1.—Log  $\rho$  vs. log % CaF<sub>2</sub> added to CdF<sub>2</sub>:Y<sup>3+</sup> crystals at 300 and 77°K.

the 0% CaF<sub>2</sub> untreated spectrum. There is one noticeable difference, however. The large absorption peak at 9760 Å in the 0% CaF<sub>2</sub> curve has almost disappeared in the 7% CaF<sub>2</sub> sample. The reason for this single large absorption peak in YbF<sub>3</sub>-doped CdF<sub>2</sub> is not fully understood, nor is its drastic reduction in intensity upon addition of CaF<sub>2</sub> to CdF<sub>2</sub>.

The behavior of the infrared absorption of Cd-fired crystals of Cd<sub>1-x</sub>Ca<sub>x</sub>F<sub>2</sub>:0.1% YF<sub>3</sub> and CdF<sub>2</sub>:x% YF<sub>3</sub> was similar to that for Yb doping. Between 1 and 10% CaF<sub>2</sub> or YF<sub>3</sub>, the crystals changed from blue to colorless.

**Visible Fluorescence, Phosphorescence, and Thermoluminescence.**—Visible fluorescent, phosphorescent, and thermoluminescent radiations under 2537- and 3660-Å excitation (low-pressure Hg pen lamps) were observed visually. Generally, the 2537-Å

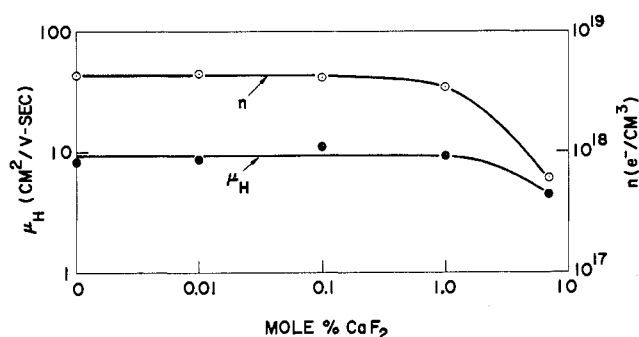


Figure 2.—Log  $n$  vs. log %  $\text{CaF}_2$  and log  $\mu_H$  vs. log %  $\text{CaF}_2$  for the samples in Figure 1 at 300°K.

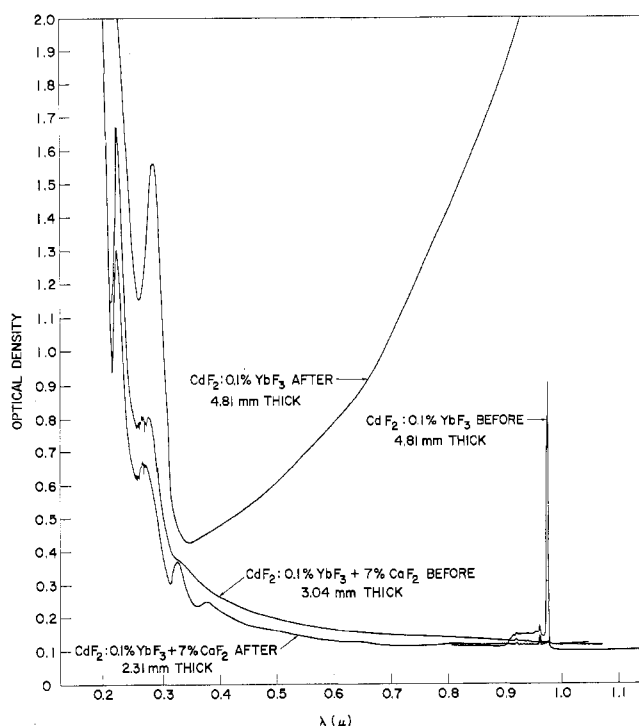


Figure 3.—Absorption spectra for  $\text{Cd}_{1-x}\text{Ca}_x\text{F}_2:1\% \text{YbF}_3$  crystals before and after firing in Cd at 500°.

line was the more efficient source although the 3660-Å line did excite observable emissions in the  $\text{CaF}_2$ - $\text{CdF}_2$  mixed crystals. The thermoluminescence was observed by allowing the sample to warm naturally to room temperature after ultraviolet irradiation at 77°K.

Typical results under 2537-Å excitation follow for  $\text{Cd}_{1-x}\text{Ca}_x\text{F}_2:0.1\% \text{YF}_3$  crystals. The fluorescence of untreated crystals changed from weak pink to yellow to whitish at 1, 3, and 10%  $\text{CaF}_2$ , respectively. The fluorescent intensities were about equal at 300 and 77°K, but Cd firing quenched only the 300° emissions. The 300° phosphorescence changed from yellow to yellow-green to whitish while that at 77°K became weaker yellow-gold at 1, 3, and 10%  $\text{CaF}_2$ . The phosphorescent lifetimes of untreated crystals were much longer at 77 than at 300°K—minutes as compared to seconds—except in the 10%  $\text{CaF}_2$  sample in which they were about equal. The lifetimes increased progressively as the  $\text{CaF}_2$  crystal content increased from 3 to 7 to 10%. The thermoluminescence, from 77 to 300°K, was bright yellow between 0 and 7%  $\text{CaF}_2$  and white at 10%  $\text{CaF}_2$ . At  $\text{CaF}_2$  concentrations less than 7%, Cd firing quenched both the phosphorescence and thermoluminescence.

**Divalent Ions.**—Optical absorption studies on Sm-doped crystals, both untreated and Cd fired, over the entire  $\text{CaF}_2$ - $\text{CdF}_2$  solid solution range indicated the presence of  $\text{Sm}^{2+}$  only at very

high  $\text{CaF}_2$  concentrations. With about 0.2% total Sm, no  $\text{Sm}^{2+}$  could be obtained in the crystals unless the  $\text{CaF}_2$  content was 99.5% or greater. Similar results were found with  $\text{YF}_3$  doping and also with  $\text{YbF}_3$  doping up to about 7%  $\text{CaF}_2$ . At this concentration there was some indication of  $\text{Yb}^{2+}$  ions as seen by the ultraviolet absorption bands centered around 2170, 2650, 3250, and 3750 Å in Figure 3. These bands became stronger upon Cd firing. Absorption studies on  $\text{Yb}^{2+}$  in  $\text{CaF}_2$ <sup>12</sup> found bands centered around 2200, 2470, 2620, 2730, 3080, and 3650 Å. A strong yellow fluorescence at 77°K under 2537-Å excitation also appeared to be characteristic of  $\text{Yb}^{2+}$ .

## Discussion

The reasons for the rapid transitions in the conductivity, the associated infrared absorption, and the phosphorescent lifetimes in a specific  $\text{CaF}_2$  concentration region in the  $\text{Cd}_{1-x}\text{Ca}_x\text{F}_2:\text{RE}^{3+}$  crystals along with the production of  $\text{RE}^{2+}$  ions at varying compositions—not necessarily the 1 to 10%  $\text{CaF}_2$  region—are considered below using the model proposed previously for  $\text{CdF}_2:\text{RE}^{3+}$  crystals.<sup>10</sup>

**Conductivity, Infrared Absorption, and Phosphorescence.**—The donor level proposed for the conducting  $\text{CdF}_2:\text{RE}^{3+}$  crystals consists of an electron being shared by the  $\text{Cd}^{2+}$  nearest neighbors to the substituted  $\text{RE}^{3+}$  dopant. The donor can be identified with a "resonance" stabilized  $\text{Cd}^+$  oxidation state. This illustrates a significant difference between  $\text{CaF}_2$  and  $\text{CdF}_2$ , one that allows for a shallow donor level. The 1+ oxidation state is much more stable for Cd than for Ca. Generally,  $\text{Cd}^+$  needs to be stabilized somewhat to prevent disproportionation. This can be accomplished in the conducting  $\text{CdF}_2:\text{RE}^{3+}$  crystals by an electron being shared among several  $\text{Cd}^{2+}$  ions<sup>12</sup> near the substituted  $\text{RE}^{3+}$ . The stabilized Cd "impurity" state provides a natural shallow donor level (hydrogenic possibly)<sup>8</sup> in Cd-fired  $\text{CdF}_2:\text{RE}^{3+}$  crystals.

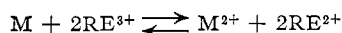
When the Cd "resonance" network is disrupted, the "impurity" state can no longer be formed. Consequently, there can be no conductivity. This is what happens when  $\text{CaF}_2$  is added to the  $\text{CdF}_2:\text{RE}^{3+}$  system or the  $\text{RE}^{3+}$  dopant concentration is increased. As seen above, the resistivity, Hall mobility, carrier concentration, and broad infrared absorption all undergo sharp changes between 1 and 10%  $\text{CaF}_2$  or  $\text{RE}^{3+}$  dopant concentration. Apparently, the impurity level giving rise to conduction and blue crystals is destroyed by replacing about one in every ten  $\text{Cd}^{2+}$  ions with another ion, such as  $\text{Ca}^{2+}$  or  $\text{RE}^{3+}$ , that cannot participate in the "resonance" effect.

The phosphorescent behavior also supports the proposed conductivity model. The phosphorescent lifetimes in the unfired crystals increase from seconds to minutes in the 1 to 10%  $\text{CaF}_2$  concentration region. This can be explained as proposed previously.<sup>10</sup> The electron excited by ultraviolet radiation is trapped in the Cd "impurity" levels until recombination can occur. As the  $\text{CaF}_2$  content increases from 1 to 10%, the number of "impurity" states decreases and their physical separation increases. It then takes longer for re-

combination to occur, and the phosphorescent lifetimes increase.

**Divalent Rare Earths.**—The case for  $RE^{2+}$  ions in  $CdF_2$  hosts has been discussed previously.<sup>10</sup> Since  $Cd^{2+}$  is rather easily reduced and  $Ca^{2+}$  is not,  $RE^{2+}$  ions can be obtained in  $CaF_2$  but not  $CdF_2$ . Any agent strong enough to reduce  $RE^{3+}$  to  $RE^{2+}$  can reduce the  $CdF_2$  host more easily. Hence, Ca vapor firings produce  $RE^{2+}$  ions in  $CaF_2$  while Cd vapor does not produce  $RE^{2+}$  ions (except  $Eu^{2+}$ ) in  $CdF_2$ .

A qualitative estimate of the stability of various oxidation states in these highly ionic solids can be obtained from the values of the oxidation potentials for the appropriate reactions. From the appropriate potentials it can be seen that in the reaction



the products are favored for Ca plus  $CaF_2$  while the reactants are favored with Cd plus  $CdF_2$ .

In the  $CaF_2$ - $CdF_2$  solid solution region the  $RE^{2+}$  concentrations obtained by the above reaction will change. Consider the equilibrium constant for Cd firing  $Cd_{1-x}Ca_xF_2:RE^{3+}$  crystals. As  $x$  increases, the  $Cd^{2+}$  concentration decreases. Since  $P_{Cd}$  and the  $RE^{3+}$  concentration remain essentially constant, the

$RE^{2+}$  content increases. This is precisely what is observed experimentally. Divalent ytterbium is detected optically at 7%  $CaF_2$  as is shown in Figure 3. Divalent samarium, being considerably less stable than  $Yb^{2+}$ , was not observed until the  $CdF_2$  content was very low.

Then the occurrence of various  $RE^{2+}$  ions at different compositions in the  $CaF_2$ - $CdF_2$  solid solution region upon Cd firing at 500° can be explained on the basis of the relative stability of the  $RE^{2+}$  and  $Cd^{2+}$  oxidation states as indicated by their oxidation potentials. The concentration of  $RE^{2+}$  ions in the solid solutions can be increased by decreasing the  $Cd^{2+}$  concentration. However, except for  $Eu^{2+}$  and  $Yb^{2+}$ , no  $RE^{2+}$  can be obtained in the solid solutions except at very low  $CdF_2$  contents. The presence of optically detectable  $RE^{2+}$ , then, does not necessarily correspond with the conductivity, infrared absorption, and phosphorescent lifetime changes that occur in the 1 to 10%  $CaF_2$  region of the  $CdF_2$ - $CaF_2$  solid solutions.

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## Semiconductivity in $Cd_{1-x}Ca_xF_2:In^{3+}$ Single Crystals

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Bridgman-grown  $Cd_{1-x}Ca_xF_2$  single crystals were doped with 0.1 mole %  $In_2O_3$ ,  $Ga_2O_3$ , and  $Tl_2O_3$ . Heat treating the crystals in a Cd atmosphere at 500° had no effect on the resistivity (about  $10^7$  ohm-cm) of the Ga- and Tl-doped crystals. However, with In-doped crystals Cd firing turned the colorless insulators into dark red, n-type semiconductors. The 300°K resistivity, carrier concentration, and mobility were about 10 ohm-cm,  $10^{17}$  e<sup>-</sup>/cm<sup>3</sup>, and 10 cm<sup>2</sup>/v-sec, respectively. At 77°K the crystals had high resistivity (about  $10^8$  ohm-cm). Two activation energies for conduction of 0.15 and 0.20 ev appeared to be present. The dark red crystal color, associated with the conductivity, was caused by the combination of strong infrared and visible absorptions. Yellow-green phosphorescent and thermoluminescent emissions in untreated, In-doped crystals were excited with 2537-A radiation. All of the above properties were strongly dependent on the  $CaF_2$  content of the doped  $Cd_{1-x}Ca_xF_2$  crystals. Between 0 and 1%  $CaF_2$  there was little change in the properties. Between 1 and 10%  $CaF_2$  the resistivity increased from 10 to  $10^8$  ohm-cm, the carrier concentration and mobility became unmeasurable, the crystal color changed from dark red to colorless, and the phosphorescent lifetimes increased from seconds to minutes. Since the properties exhibited by the In-doped  $Cd_{1-x}Ca_xF_2$  crystals are quite similar to those previously found for RE-doped crystals, it appears that the same conductivity model previously proposed for  $CdF_2:RE^{3+}$  crystals is also applicable for  $In^{3+}$  doping. The stability of the lower oxidation states of In can account for the differences between In and RE doping.

### Introduction

When  $CdF_2$  crystals are doped with rare earth elements (except La, Ce, Pr, and Eu), yttrium, or scandium and fired in Cd vapor at 500°, they switch from electrical insulators (resistivity about  $10^7$  ohm-cm at 300°K) to n-type semiconductors (resistivity about 1 ohm-cm at 300°K).<sup>2-4</sup> Simultaneously, the crystals

become deep blue. The temperature dependence of the the resistivity, Hall coefficient, and Hall mobility indicate impurity conduction.<sup>4,5</sup> In  $CdF_2$ - $CaF_2$  mixed crystals doped with rare earths, the properties obtained by Cd firing are strongly dependent on the  $CaF_2$  content.<sup>6</sup> Between 1 and 10%  $CaF_2$  the crystals change from blue conductors to colorless insulators.

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